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Sheet 1 of 1

Complete if Known	
Application Number	10/716755
Filing Date	November 19, 2003
First Named Inventor	Tang, Stephen
Group Art Unit	~~2818~~ 2827
Examiner Name	~~Unknown~~ S. MAI
Attorney Docket No: 80107.038US1	

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
SM		FAZAN, PIERRE, et al., "A Simple 1-Transistor Capacitor-Less Memory Cell for High Performance Embedded DRAMs", IEEE 2002 Custom Integrated Circuits Conference, (2002),99-102	
SM		OHSAWA, TAKASHI, et al., "A Memory Using One-Transistor Gain Cell on SOI(FBC) with Performance Suitable for Embedded DRAM's", 2003 Symposium on VLSI Circuits Digest of Technical Papers, (2003),4 pages	
SM		OHSAWA, TAKASHI, et al., "Memory Design Using a One-Transistor Gain Cell on SOI", IEEE Journal of Solid-State Circuits, vol. 37, no. 11, (November 2002),1510-1522	
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EXAMINER SON MAI **DATE CONSIDERED** 05-03-05

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